

Supporting Information

p-type Mesoscopic NiO as an Active Interfacial Layer for Carbon
Counter Electrodes Based Perovskite Solar Cells

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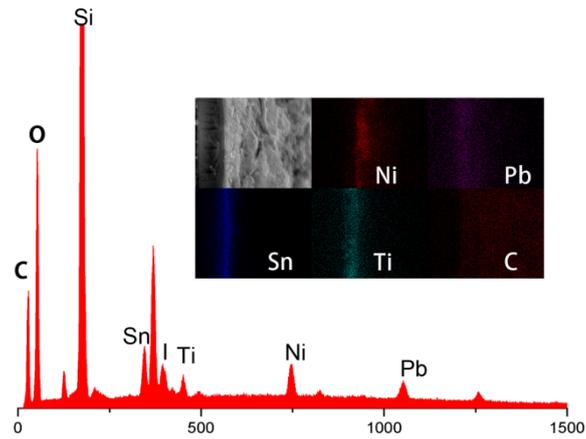


Fig. S1 Cross-sectional scanning electron micrograph (SEM) of $\text{TiO}_2/\text{NiO}(\text{CH}_3\text{NH}_3\text{PbI}_3)/\text{carbon}$ device and energy-dispersive x-ray (EDX) spectroscopy with elemental mapping of Ni, Ti, Pb, Sn and C.

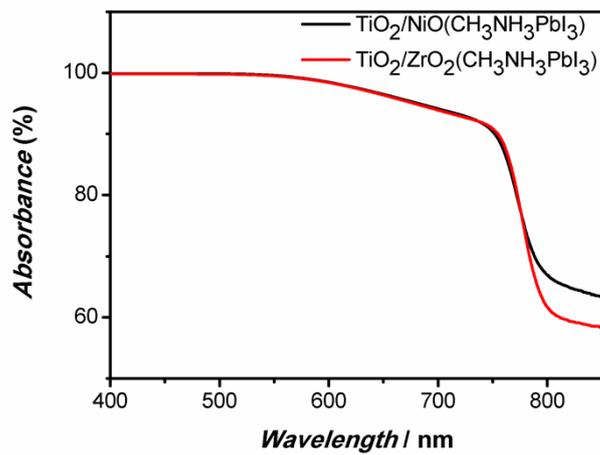


Fig. S2 The absorbance of $\text{TiO}_2/\text{NiO}(\text{CH}_3\text{NH}_3\text{PbI}_3)$ films and $\text{TiO}_2/\text{ZrO}_2(\text{CH}_3\text{NH}_3\text{PbI}_3)$ films, the $\text{CH}_3\text{NH}_3\text{PbI}_3$ was deposited using two-step sequential deposition method.

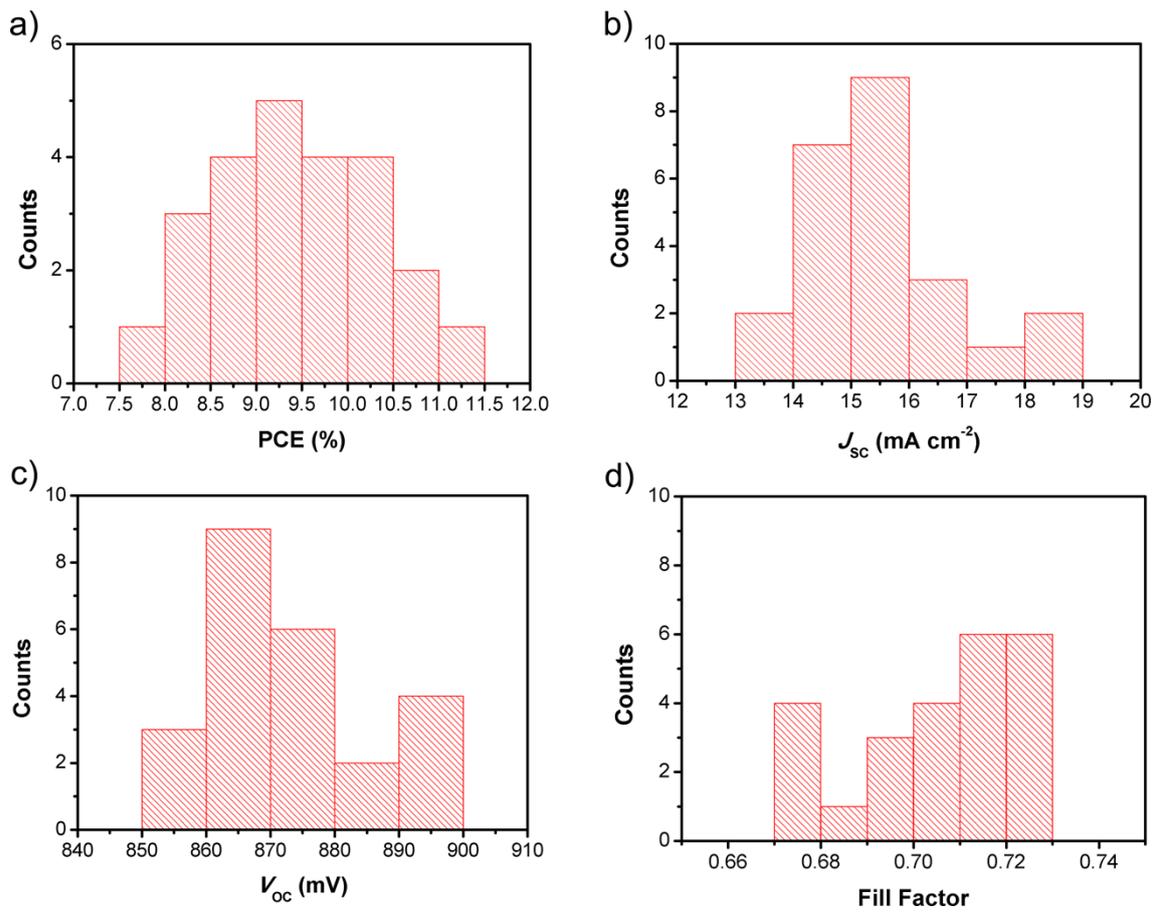


Fig. S3 Summary of photovoltaic parameters of 24 pieces of $\text{TiO}_2/\text{NiO}(\text{CH}_3\text{NH}_3\text{PbI}_3)/\text{carbon}$ devices: a) power conversion efficiency (PCE), b) short-circuit current density (J_{sc}), c) open-circuit voltage (V_{oc}), and d) fill factor.

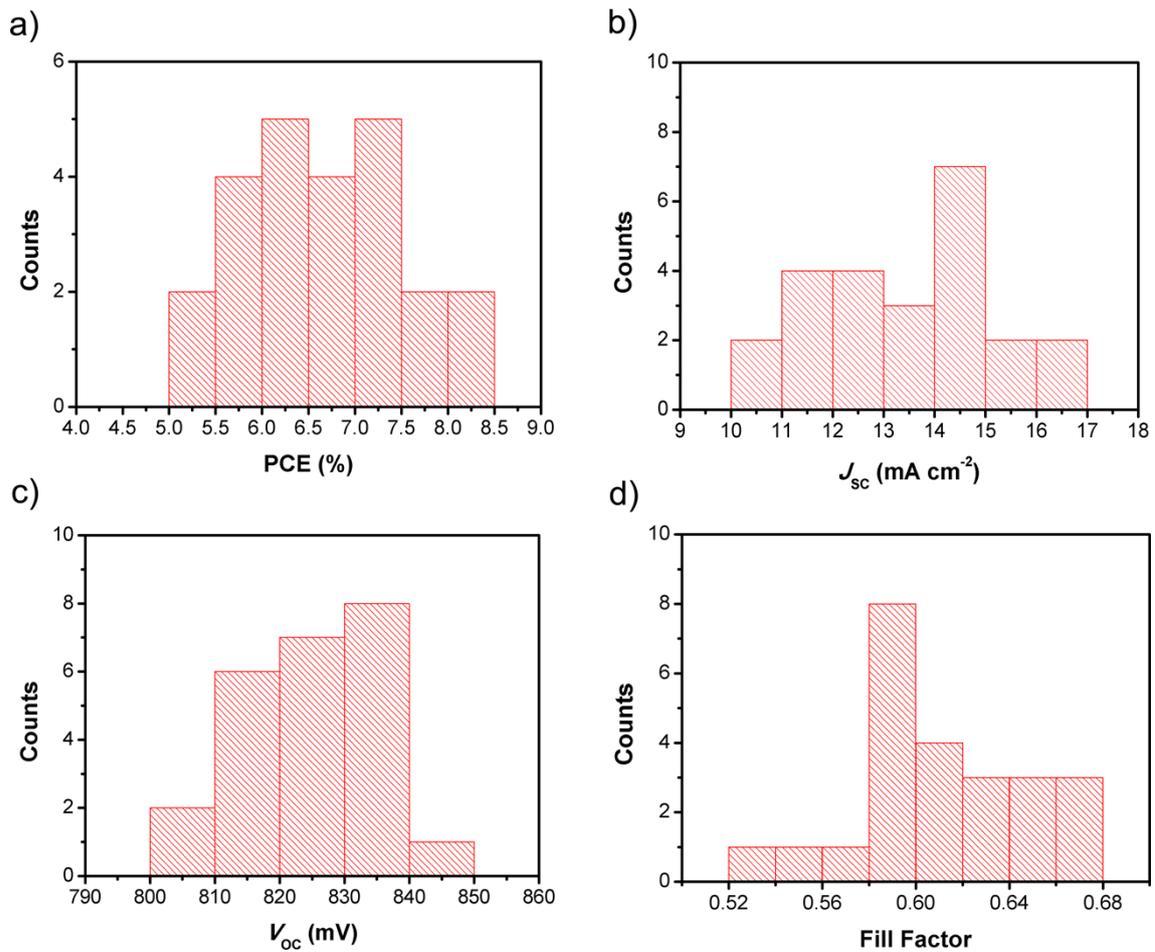


Fig. S4 Summary of photovoltaic parameters of 24 pieces of $\text{TiO}_2/\text{ZrO}_2(\text{CH}_3\text{NH}_3\text{PbI}_3)/\text{carbon}$ devices: a) power conversion efficiency (PCE), b) short circuit current density (J_{sc}), c) open circuit voltage (V_{oc}), and d) fill factor.

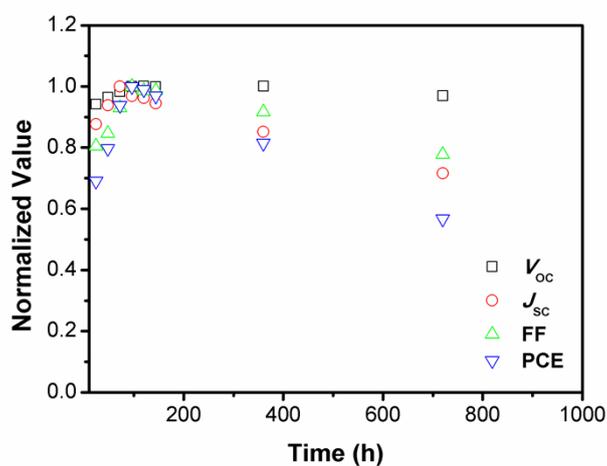


Fig. S5 The normalized photovoltaic parameters: open circuit voltage (V_{oc}), short circuit current density (J_{sc}), fill factor (FF), and power conversion efficiency of $\text{TiO}_2/\text{NiO}(\text{CH}_3\text{NH}_3\text{PbI}_3)/\text{carbon}$ device were recorded.

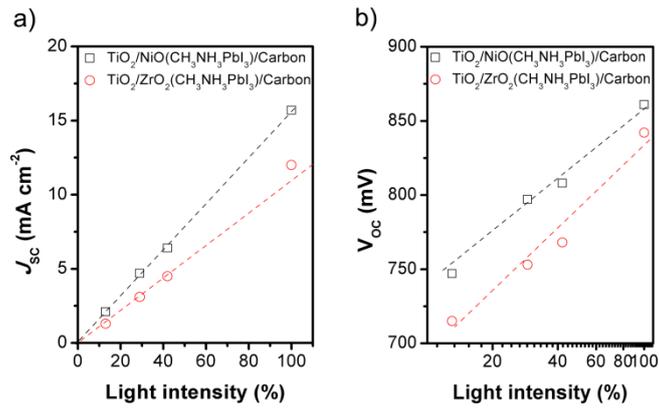


Fig. S6 a) Photo-current and b) photo-voltage response under different light intensity for $\text{TiO}_2/\text{NiO}(\text{CH}_3\text{NH}_3\text{PbI}_3)/\text{carbon}$ device (black square) and $\text{TiO}_2/\text{ZrO}_2(\text{CH}_3\text{NH}_3\text{PbI}_3)/\text{carbon}$ device (red circle).

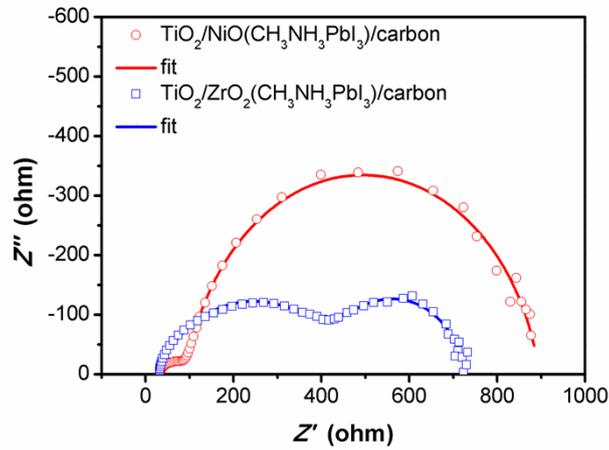


Fig. S7 Nyquist plots of $\text{TiO}_2/\text{NiO}(\text{CH}_3\text{NH}_3\text{PbI}_3)/\text{carbon}$ device (red) and $\text{TiO}_2/\text{ZrO}_2(\text{CH}_3\text{NH}_3\text{PbI}_3)/\text{carbon}$ device (blue) in the dark with bias at 0.75 V over the frequency range of 100 mHz to 2 MHz.

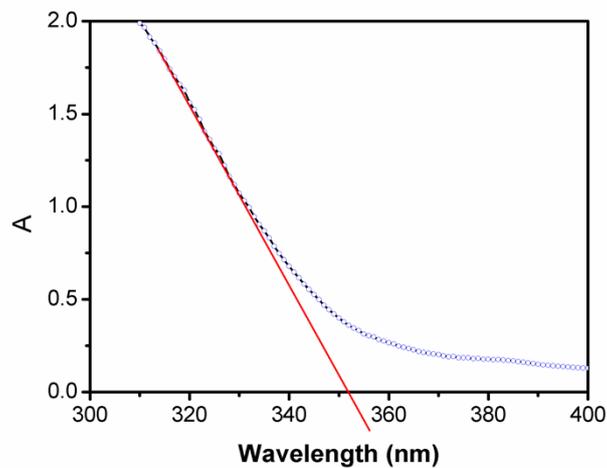


Figure S8 UV-vis spectra of NiO film and the E_g was calculated according to the equation: $E_g \approx 1240/\lambda$, showing that the NiO film have a band gap of $\sim 3.5\text{eV}$.